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having crystal grain boundaries which are discontinuous to the first polycrystalline silicon film, and a metal nitride film formed on the second polycrystalline silicon film.

2. (Amended) A semiconductor device comprising:

a pair of impurity diffused regions formed in a silicon substrate, spaced from each other; and
a gate electrode formed above the silicon substrate between the pair of impurity diffused regions
with a gate insulation film interposed therebetween, the gate electrode being formed of a first polycrystalline silicon film formed on the gate insulation film, a second polycrystalline silicon film formed on the first polycrystalline silicon film having a thickness thinner than that of the first polycrystalline silicon film and having crystal grain boundaries which are discontinuous to the first polycrystalline silicon film, a metal nitride film formed on the second polycrystalline silicon film, and a metal film formed on the metal nitride film.

ADD the following new claims:

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18. (New) A semiconductor device according to claim 1, wherein the second polycrystalline silicon film is 2-20 nm-thick. 112/1st C

19. (New) A semiconductor device according to claim 2, wherein the second polycrystalline silicon film is 2-20 nm-thick. 112/1st